

TO-92MOD Plastic-Encapsulated Transistors

2SA1283 TRANSISTOR (PNP)

FEATURE

Power dissipation

$$P_{CM} : 0.9 \text{ W (Tamb=25°C)}$$

Collector current

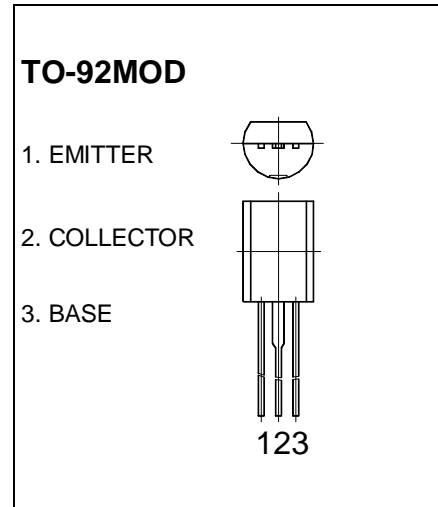
$$I_{CM} : -1 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu\text{A}, I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -2\text{mA}, I_B = 0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}, I_C = 0$	-6		V
Collector cut-off current	I_{CBO}	$V_{CB} = -50\text{V}, I_E = 0$		-0.2	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4\text{V}, I_C = 0$		-0.2	μA
DC current gain	h_{FE}	$V_{CE} = -4\text{V}, I_C = -100\text{mA}$	55	300	
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -500\text{mA}, I_B = -25\text{mA}$		-0.3	V
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_C = -10\text{mA}$	50		MHz
Output capacitance	C_{ob}	$V_{CE} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		25	pF

CLASSIFICATION OF h_{FE}

Rank	C	D	E
Range	55-110	90-180	150-300